



# Bipolar PNP Bare Die – BTP6066

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## Part Description

The BTP6066 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6066

## Key Parameters:

- VCBO = -120V
- VCEO = -100V
- VEBO = -6V
- hFE = 140-330 @ VCE = -2V, IC = -0.15A
- VCE(Sat) = -0.5V @ IC = -0.5A, IB = -50mA
- fT = 100 MHz @ VCE = -5V, IE = 0A
- COBO = 10pF @ VCB = -10V

## Features

Low VCE(sat)

## Die Size (Unawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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